

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 CFR § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked-up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(c)(1)(ii). Any claim not accompanied by a marked-up version has not been changed relative to the immediate prior version, except that marked-up versions are not being supplied for any added claim or canceled claim.

CLAIMS

1. (Amended) A method of forming a capacitor comprising the following steps:

B2 forming a capacitor plate, forming a capacitor plate comprising:

forming a solid mass of silicon material within an opening formed over a doped region of a silicon substrate, the mass comprising only two forms of silicon, the mass including undoped silicon in physical contact with the doped region; and

substantially selectively forming rugged polysilicon from one of the forms of silicon and not from another of the forms of silicon; and forming a cell plate proximate the rugged polysilicon.

2. The method of claim 1 wherein the two forms of silicon comprise doped silicon and undoped silicon. NE

3. The method of claim 2 wherein the doped silicon comprises a dopant concentration of at least 5×10^{18} atoms/cm³ and wherein the undoped silicon comprises a dopant concentration of less than 5×10^{18} atoms/cm³.

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4. The method of claim 2 wherein the doped silicon comprises a dopant concentration of at least 1×10^{19} atoms/cm³ and wherein the undoped silicon comprises a dopant concentration of less than or equal to 1×10^{18} atoms/cm³.

B³ 5. (Amended) A method of forming a capacitor comprising the following steps:

forming a solid mass of silicon material over a doped diffusion region of a silicon substrate, the mass comprising exposed doped silicon and exposed undoped silicon, and including undoped silicon in contact with the doped diffusion region;

substantially selectively forming rugged polysilicon from the exposed undoped silicon and not from the exposed doped silicon; and

forming a cell plate proximate the rugged polysilicon.

6. The method of claim 5 wherein the step of forming a mass of silicon material comprises forming a layer of doped silicon between two layers of undoped silicon.

7. The method of claim 5, further comprising conductively doping the undoped silicon after forming the rugged polysilicon.

8. The method of claim 5, further comprising, after forming the rugged polysilicon, out-diffusing impurity from the doped silicon into the undoped silicon to conductively dope the undoped silicon.

9. The method of claim 5 wherein the step of forming the mass comprises forming the exposed undoped silicon to be substantially amorphous.

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10. The method of claim 5 wherein the step of forming the mass comprises forming the exposed doped silicon to be substantially polycrystalline.

11. (Amended) A method of forming a capacitor comprising the following steps:

B4 forming an insulative layer over a doped region of a semiconductor substrate;

forming an opening through the insulative layer to the doped region;

forming two forms of silicon within and filling the opening, the two forms of silicon including undoped silicon in contact with the doped region;

exposing the two forms of silicon to common subsequent processing conditions which substantially selectively form rugged polysilicon from one of the exposed two forms of silicon and not from another of the exposed two forms of silicon; and

forming a cell plate proximate the rugged polysilicon.

12. The method of claim 11 wherein the two forms of silicon comprise doped silicon and undoped silicon. ~~NE~~

13. (Amended) A method of forming a capacitor comprising the following steps:

forming an insulative layer over a doped region on a semiconductor wafer substrate;

BS forming an opening through the insulative layer to the doped region;

forming silicon material within the opening, the silicon material comprising doped silicon and undoped silicon and defining a capacitor storage node, a portion of the undoped silicon being in physical contact with the doped region;

removing a portion of the insulative layer to expose a sidewall surface of the storage node, the exposed sidewall surface comprising undoped silicon;

forming HSG from the undoped silicon of the exposed sidewall surface;
and

forming a cell plate proximate the storage node.

14. The method of claim 13 wherein the doped silicon comprises polysilicon and the undoped silicon comprises substantially amorphous silicon.

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15. The method of claim 13 wherein the step of forming the silicon material comprises forming a layer of doped silicon between two layers of undoped silicon.

16. The method of claim 13 wherein the step of forming the silicon material comprises forming a layer of doped polysilicon between two layers of undoped substantially amorphous silicon.

17. (Amended) A method of forming a capacitor comprising the following steps:

forming an insulative layer over a doped region on a semiconductor substrate;

forming an opening through the insulative layer to the doped region;

forming an undoped silicon layer within the opening to narrow the opening, a portion of the undoped silicon contacting the doped region;

forming a doped silicon layer within the narrowed opening, the undoped silicon layer and doped silicon layer together defining substantially an entirety of structural material for a capacitor storage node; and

forming a cell plate proximate the storage node.

18. The method of claim 17 wherein the undoped silicon layer comprises substantially amorphous silicon.

19. The method of claim 17 wherein the doped silicon layer comprises polysilicon.

20. The method of claim 17 further comprising:
removing a portion of the insulative layer to expose a sidewall surface of the storage node comprising the undoped silicon layer; and
forming rugged polysilicon from the exposed sidewall surface.

21. The method of claim 17 further comprising:
exposing a surface of the capacitor storage node comprising undoped silicon;
exposing a surface of the capacitor storage node comprising doped silicon;
and
substantially selectively forming HSG polysilicon from the exposed capacitor storage node surface comprising undoped silicon and not from the exposed capacitor storage node surface comprising doped silicon.

22. The method of claim 21 wherein the formation of the rugged polysilicon comprises: *NE*
in situ HF cleaning of the exposed sidewall surface;
seeding the exposed sidewall surface with polysilicon; and
annealing the seeded sidewall surface at about 560°C for about 20 minutes.

23. The method of claim 21 wherein the formation of the rugged polysilicon comprises:

in situ HF cleaning of the exposed sidewall surface;

seeding the exposed sidewall surface with polysilicon;

annealing the seeded sidewall surface at about 560°C for about 20 minutes; and

a polysilicon etch after the annealing to remove any monolayers of silicon.

24. (Amended) A method of forming a capacitor comprising the following steps:

forming an insulative layer over a doped region on a semiconductor substrate;

forming an opening through the insulative layer to the doped region;

B7 forming a first undoped silicon layer within the opening to narrow the opening, a portion of the undoped silicon layer contacting the doped region;

forming a doped silicon layer within the narrowed opening to further narrow the opening;

forming a second undoped silicon layer within the further narrowed opening; the first undoped silicon layer, second undoped silicon layer and doped silicon layer together defining a capacitor storage node;

removing a portion of the insulative layer to expose a sidewall surface of the storage node comprising the first undoped silicon layer;

forming rugged polysilicon on only the exposed sidewall surface; and

forming a cell plate proximate the storage node.

25. The method of claim 24 further comprising:
exposing a surface of the capacitor storage node comprising the second undoped silicon layer;
exposing a surface of the capacitor storage node comprising the doped silicon layer; and
substantially selectively forming HSG polysilicon from the exposed capacitor storage node surface comprising undoped silicon and not from the exposed capacitor storage node surface comprising doped silicon.

44. The method of claim 1, wherein forming a cell plate comprises forming a capacitor dielectric layer and a complementary capacitor plate proximate the rugged polysilicon.

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45. The method of claim 5, wherein forming a cell plate comprises forming a capacitor dielectric layer and a complementary capacitor plate proximate the rugged polysilicon and doped silicon.

46. The method of claim 11, wherein forming a cell plate comprises:
forming a dielectric layer proximate the storage node; and
forming a cell plate layer proximate the dielectric layer.

47. The method of claim 13, wherein forming a cell plate comprises:
forming a capacitor dielectric layer proximate the storage node; and
forming a complementary capacitor plate proximate the capacitor dielectric layer.

48. The method of claim 17, wherein forming a cell plate comprises:
forming a capacitor dielectric layer proximate the storage node; and
forming a complementary capacitor plate proximate the capacitor dielectric layer.

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49. The method of claim 24, wherein forming a cell plate comprises:
forming a dielectric layer proximate the storage node; and
forming a cell plate layer proximate the dielectric layer.

50. A method of forming a capacitor comprising:
forming an insulative layer over a doped region formed on a semiconductor substrate;
forming an opening through the insulative layer to the doped region;
filling the opening with silicon material, the silicon material comprising doped silicon and undoped silicon and defining a capacitor storage node;
removing a portion of the insulative layer to expose a sidewall surface of the storage node, the exposed sidewall surface comprising undoped silicon;
forming HSG from the undoped silicon of the exposed sidewall surface;
and
forming a cell plate proximate the storage node.

51. The method of claim 50, wherein forming a cell plate comprises:
forming a capacitor dielectric layer proximate the storage node; and
forming a complementary capacitor plate proximate the capacitor dielectric layer.

52. The method of claim 50 wherein the doped silicon comprises polysilicon and the undoped silicon comprises substantially amorphous silicon.

53. The method of claim 50 wherein forming the silicon material comprises forming a layer of doped silicon inside a layer of undoped silicon.

54. The method of claim 50 wherein filling the opening with silicon material comprises forming a layer of doped polysilicon within a layer of undoped substantially amorphous silicon.

55. A method of forming a capacitor comprising:
forming an insulative layer over a doped region formed on a semiconductor substrate;
forming an opening through the insulative layer to the doped region;
forming an undoped silicon layer within the opening to narrow the opening;
filling the narrowed opening with a doped silicon layer, the undoped silicon layer and doped silicon layer together defining a capacitor storage node; and
forming a cell plate proximate the storage node.

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56. The method of claim 55, wherein forming a cell plate comprises forming a capacitor dielectric layer proximate the storage node; and forming a complementary capacitor plate proximate the capacitor dielectric layer.

57. The method of claim 55 further comprising:
exposing a surface of the capacitor storage node comprising undoped silicon;
exposing a surface of the capacitor storage node comprising doped silicon;
and
substantially selectively forming HSG polysilicon from the exposed capacitor storage node surface comprising undoped silicon and not from the exposed capacitor storage node surface comprising doped silicon.

58. The method of claim 57 wherein forming HSG polysilicon comprises:
in situ HF cleaning of exposed doped and undoped silicon surfaces;
seeding the exposed undoped silicon surface with polysilicon; and
annealing the seeded surface at about 560°C for about 20 minutes.

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59. The method of claim 57 wherein forming HSG polysilicon comprises:
in situ HF cleaning of the exposed doped and undoped silicon surfaces;
seeding the exposed undoped silicon surface with polysilicon;
annealing the seeded surface at about 560°C for about 20 minutes; and
a polysilicon etch after the annealing to remove any monolayers of silicon.